### **Optical Emitter and Sensor Pair**

OPB100Z, OPB100-EZ, OPB100-SZ



#### Features:

- Infrared LED emitter
- Silicon phototransistor sensor
- Snap-in mounting
- Variable sensing distance over 36" (91.4 cm)
- Low profile package
- 24" (61.0 cm) wire leads



### Description:

The **OPB100Z** series consists of an infrared LED (**OPB100-EZ**) and phototransistor (**OPB100-SZ**) in separate plastic housings. The low cost, snap-in design requires no screws or other mounting hardware for ease of installation.

The emitter and sensor are not apertured, which allows separation distances in excess of 36" (91.4 cm) without concern for precise alignment. The front side clip allows mounting of the product to any 0.059" (1.50 mm) thick material.

This product is designed for general switching and low-speed data communications applications.

### Applications:

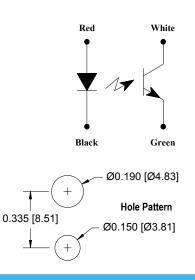
- Non-contact reflective object
- Non-contact interruptive sensing

Emitter (LED)

- Assembly line automation
- Machine automation
- Machine safety

	Ordering Information									
	Part Number	LED Peak Wavelength	Sensor	Lead Length / Spacing						
0	PB100-EZ	880 nm		24" / 26 AWG						
0	PB100-SZ		Transistor	Wire						
(	OPB100Z	00Z Contains both OPB100-EZ & OPB100								

#### **GREEN WIRE** EMITTER **Phototransistor** 0.20 24" Min. WHITE WIRE COLLECTOR **RED WIRE** ANODE Ø.184±.006 Ø0.18 BLACK WIRE -.335±.005 Hole Pattern Ø0.140±0.005 **Hole Pattern** SNAP BODY $2 \text{X.061}^{+.002}_{-.001}$ 0.11 0.34±0.015 **26 AWG** Symbolize Cover 0.32 **UL Rated**



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Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)									
Storag	-40° C to +85° C								
Opera	-40° C to +80° C								
Input LED (OP298 for additional information)									
Forwa	100 mA								
Peak F	1 A								
Revers	2 V								
Power	142 mW								
Output Phototransistor (OP598 for additional information)									
Collect	30 V								
Emitte	5 V								
Collect	50 mA								
Power	250 mW								
Electrical Characteristics (T <sub>A</sub> = 25° C unless otherwise noted)									
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS			
Input Diode (See OP298 for additional information — for reference only)									
V <sub>F</sub>	Forward Voltage	-	-	1.7	V	I <sub>F</sub> = 20 mA			
I <sub>R</sub>	Reverse Current	-	-	15	μΑ	V <sub>R</sub> = 10 V			
q <sub>HP</sub>	Emission Angle at Half Power Points	-	25	-	Degree	I <sub>F</sub> = 20 mA			
E <sub>E</sub> (APT)	Apertured Radiant Intensity	6.5	-	-	mW/ cm²	I <sub>F</sub> = 100 mA Distance = 1.43" (3.63 cm) Aperture = 0.25" (6.35 mm)			
Output Ph	ototransistor (See OP598 for additional info	rmatio	n — for	referen	ce only)				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_C = 1 \text{ mA, } E_E = 0 \text{mw/cm}^2 \text{ (no light)}$			
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage	5	-	-	V	$I_C = 100 \mu A$ , $E_E = 0 \text{mw/cm}^2$ (no light)			
I <sub>CEO</sub>	Collector Dark Current	-	-	100	nA	$V_{CE} = 10V, I_F = 0, E_E = 0 \text{ mw/cm}^2$ (no light)			
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	-	-	0.4	V	$I_C = 400 \mu A, E_E = 1.7 \text{ mw/cm}^2$			
I <sub>C(ON)</sub>	On-State Collector Current	5	-	-	mA	V <sub>CE</sub> = 5 V, E <sub>E</sub> =	= 1.7 mw/cm <sup>2</sup>		

### Notes:

- 1. Derate linearly 3.33 mW/°C above 25°C.
- 2. All parameters measured using pulse technique.
- Derate linearly 1.43 mW/°C above 25°C.

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# Performance Output Current vs. Distance

